

MICROWAVE POWER GAAS FET

TIM1011-8ULA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- **-BROAD BAND INTERNALLY MATCHED FET**
- **HIGH POWER**

P1dB= 39.5dBm at 10.7GHz to 11.7GHz

HIGH GAIN

G1dB= 9.0dB at 10.7GHz to 11.7GHz

LOW INTERMODULATION DISTORTION

IM3= -45dBc at Pout= 27.0dBm

Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 2.0A f = 10.7 to 11.7GHz	dBm	38.5	39.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0	_
Drain Current	IDS1		Α		2.0	2.5
Gain Flatness	ΔG		dB		_	±0.8
Power Added Efficiency	ηadd		%	_	39	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 27.0dBm, ∆f= 5MHz	dBc	-42	-45	_
Drain Current	IDS2	(Single Carrier Level)	Α	_	2.0	2.5
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_		80

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.4A	S	_	2.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 72mA	V	-0.5	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	4.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -72μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	3.0	3.7

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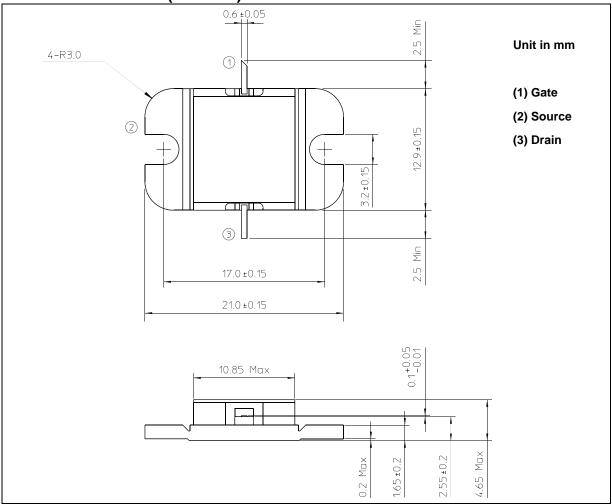


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	5.7
Total Power Dissipation (Tc= 25°C)	PT	W	40.5
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11C1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.